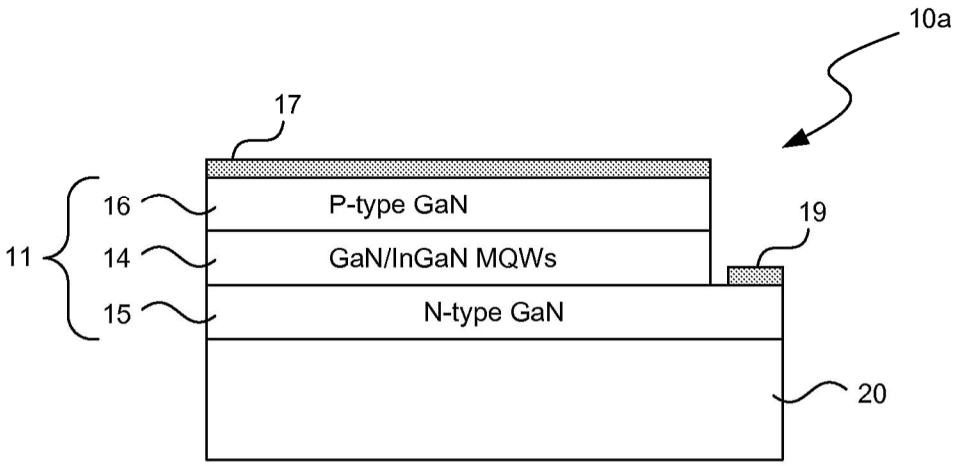


FIG. 1A
(Prior Art)

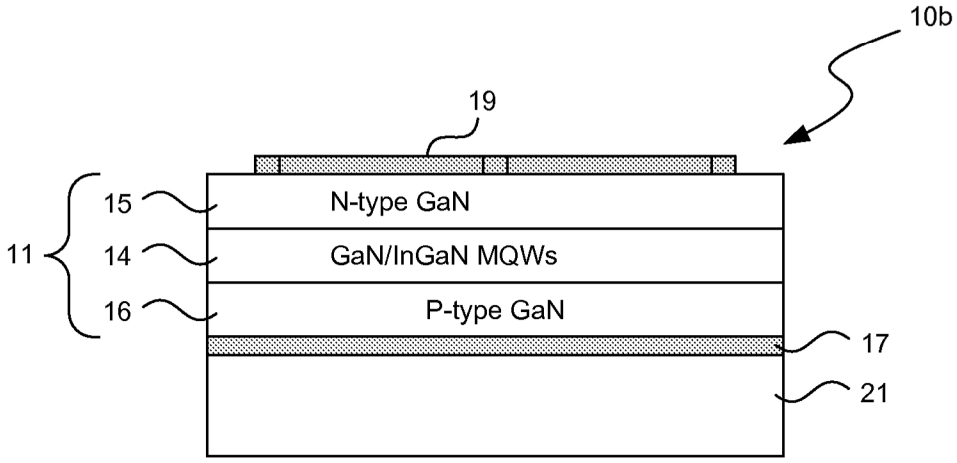


FIG. 1B
(Prior Art)

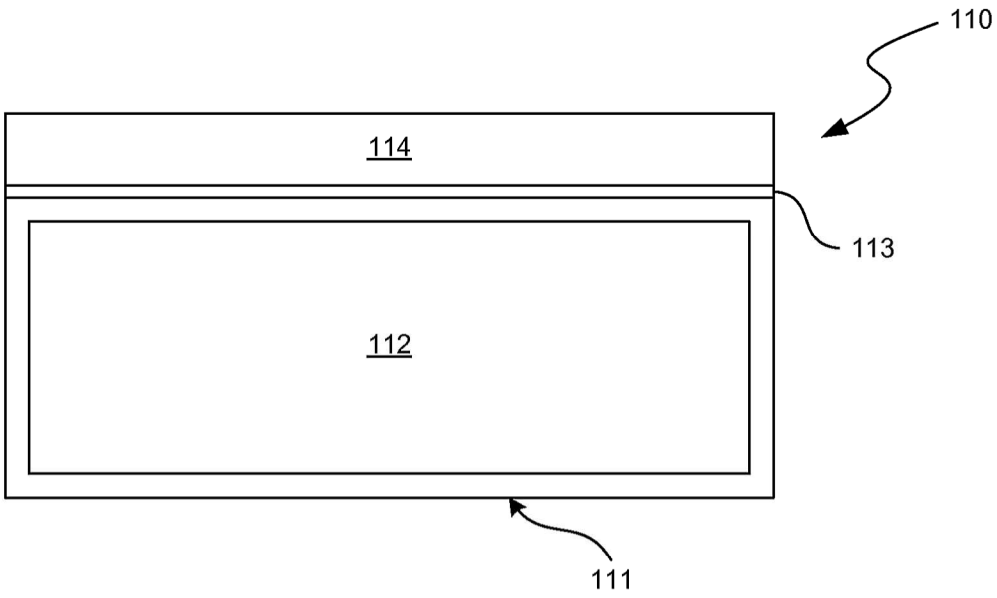


FIG. 2

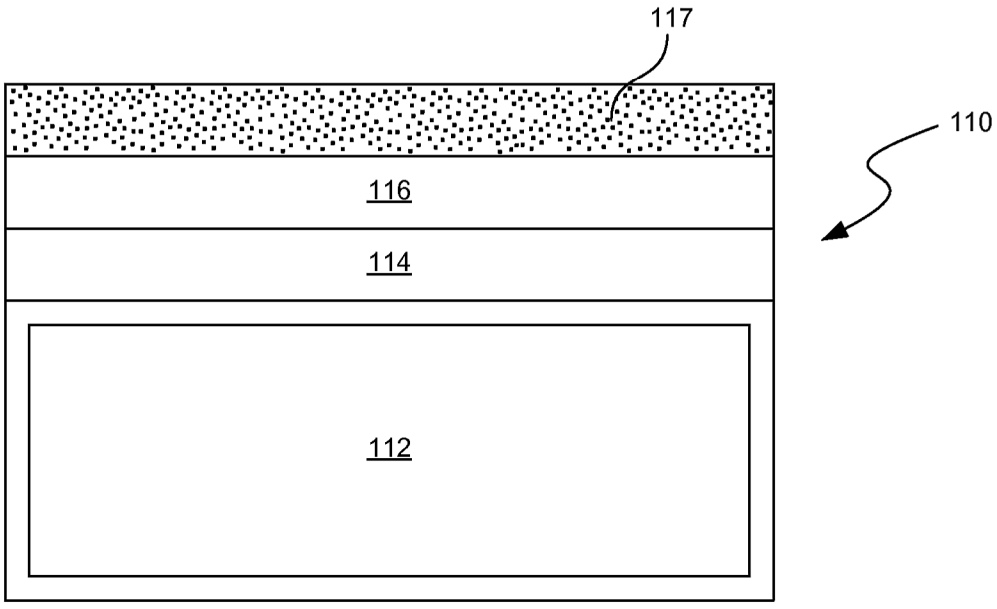


FIG. 3

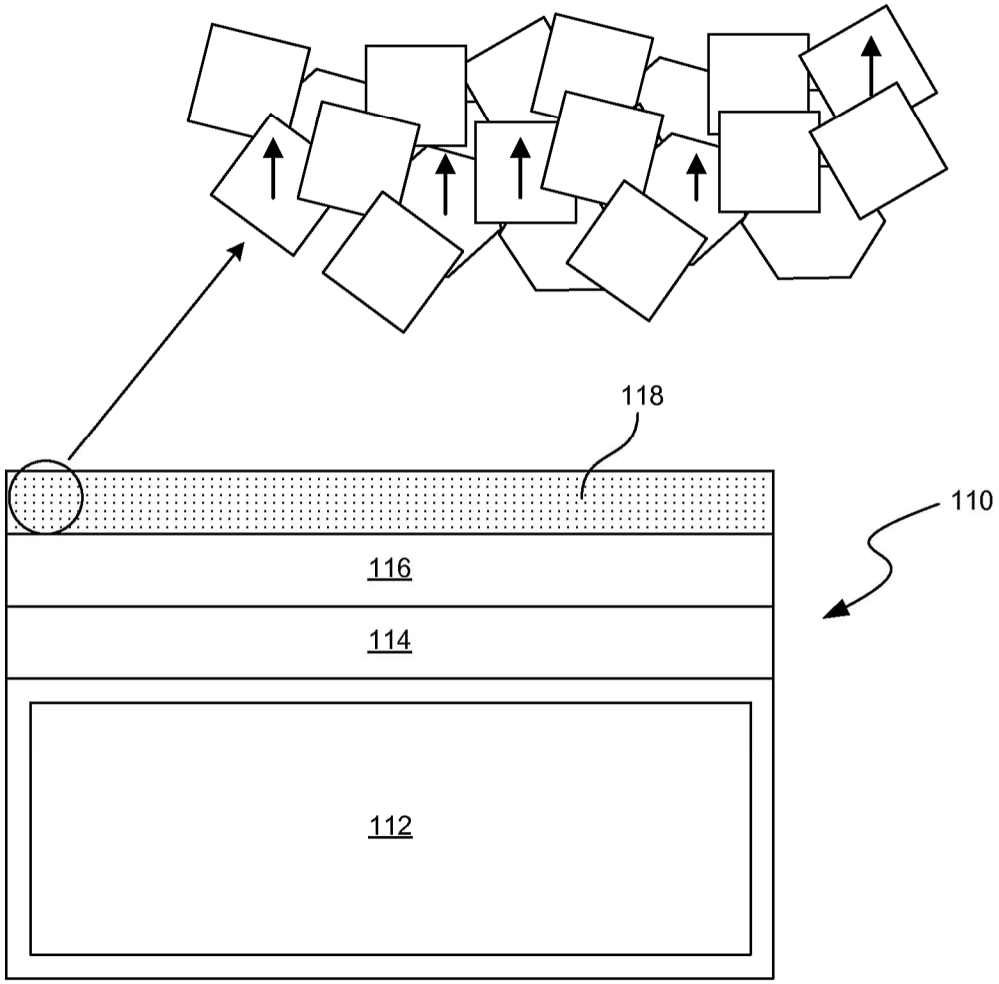


FIG. 4A

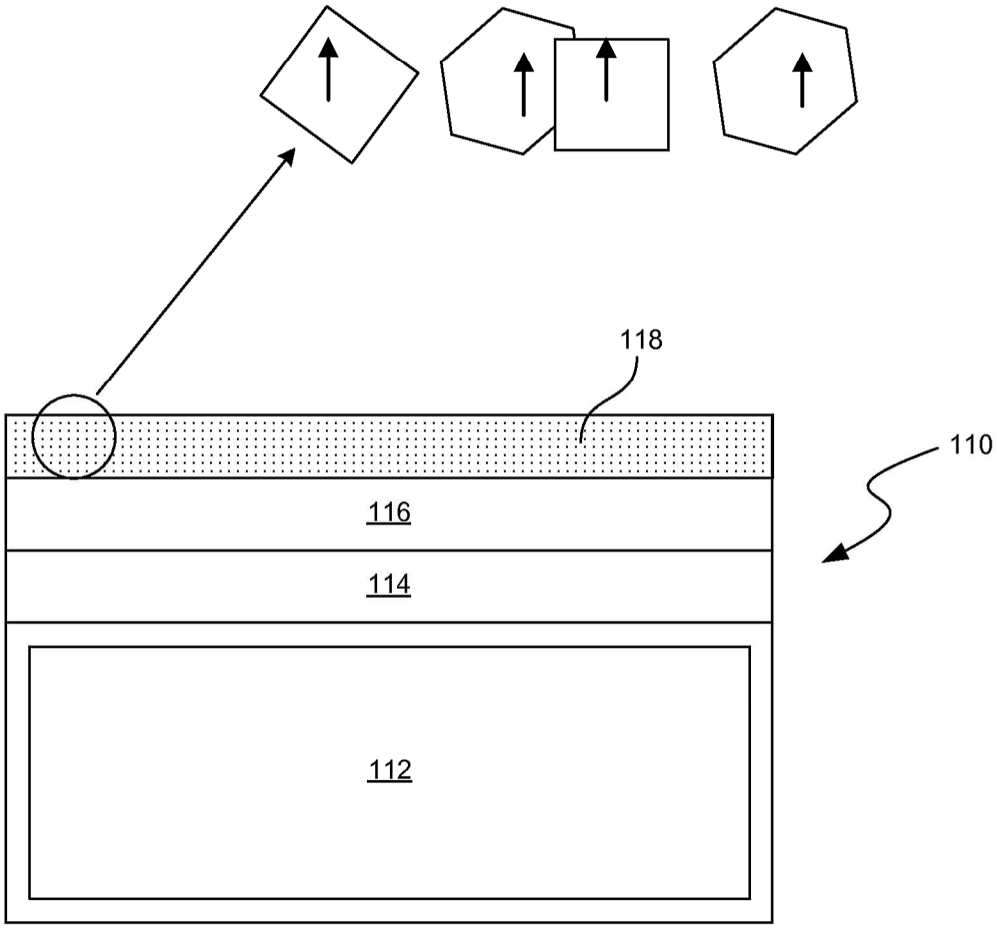


FIG. 4B

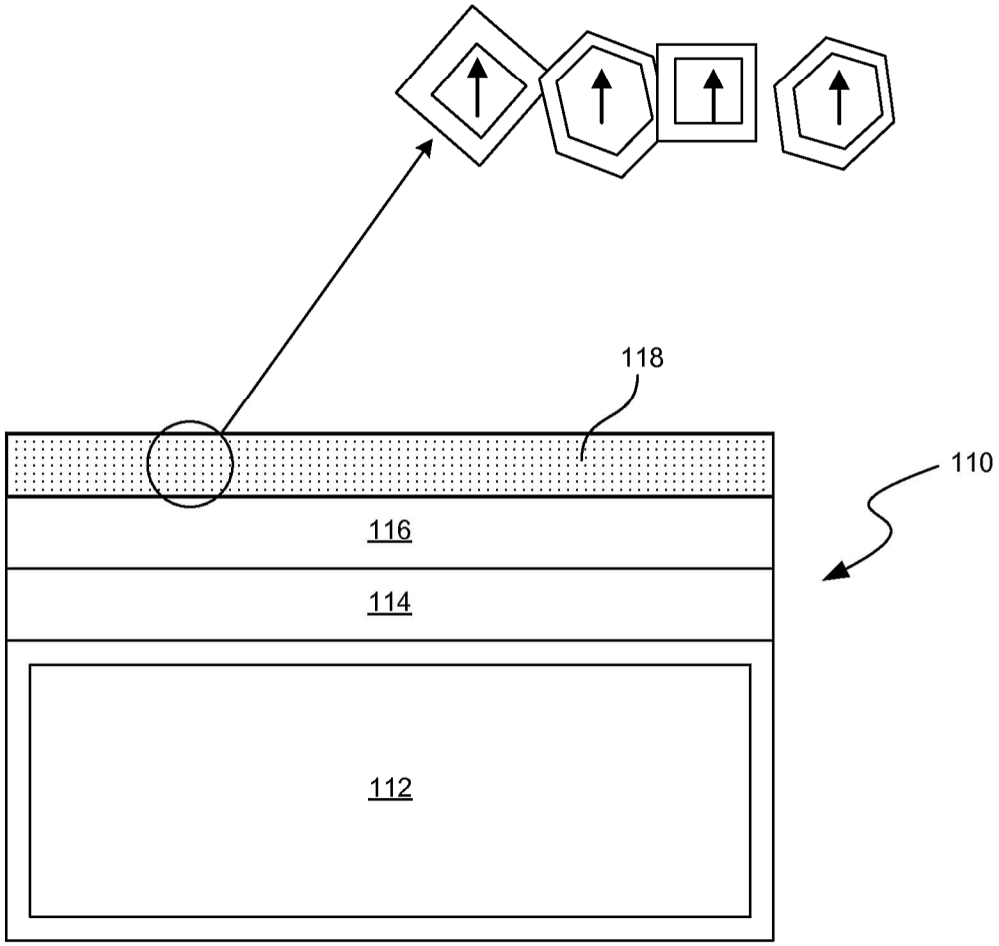


FIG. 4C

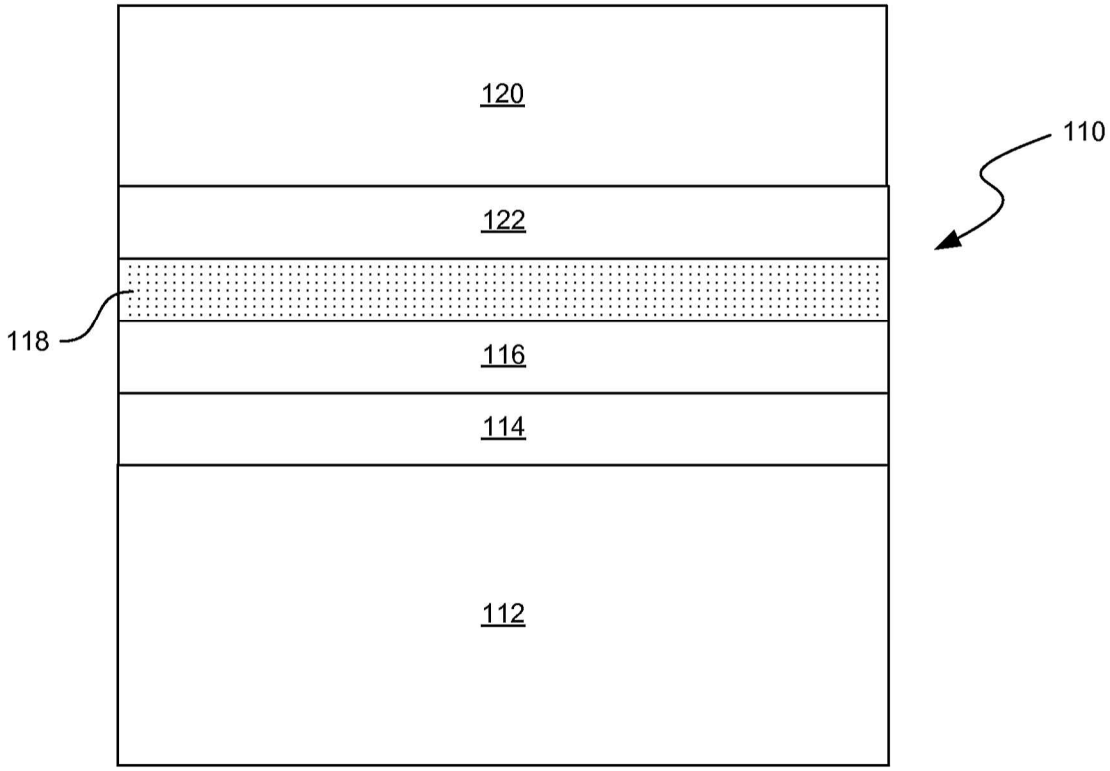


FIG. 5

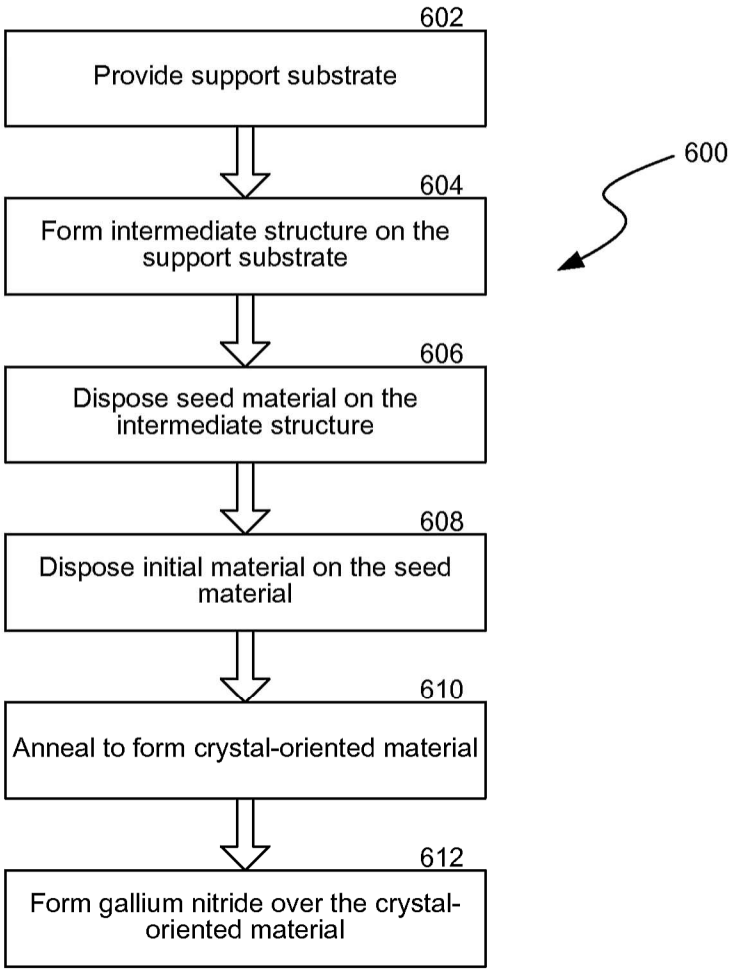

602
Provide support substrate
600
604
Form intermediate structure on the support substrate
606
Dispose seed material on the intermediate structure
608
Dispose initial material on the seed material
610
Anneal to form crystal-oriented material
612
Form gallium nitride over the crystal-oriented material

FIG. 6

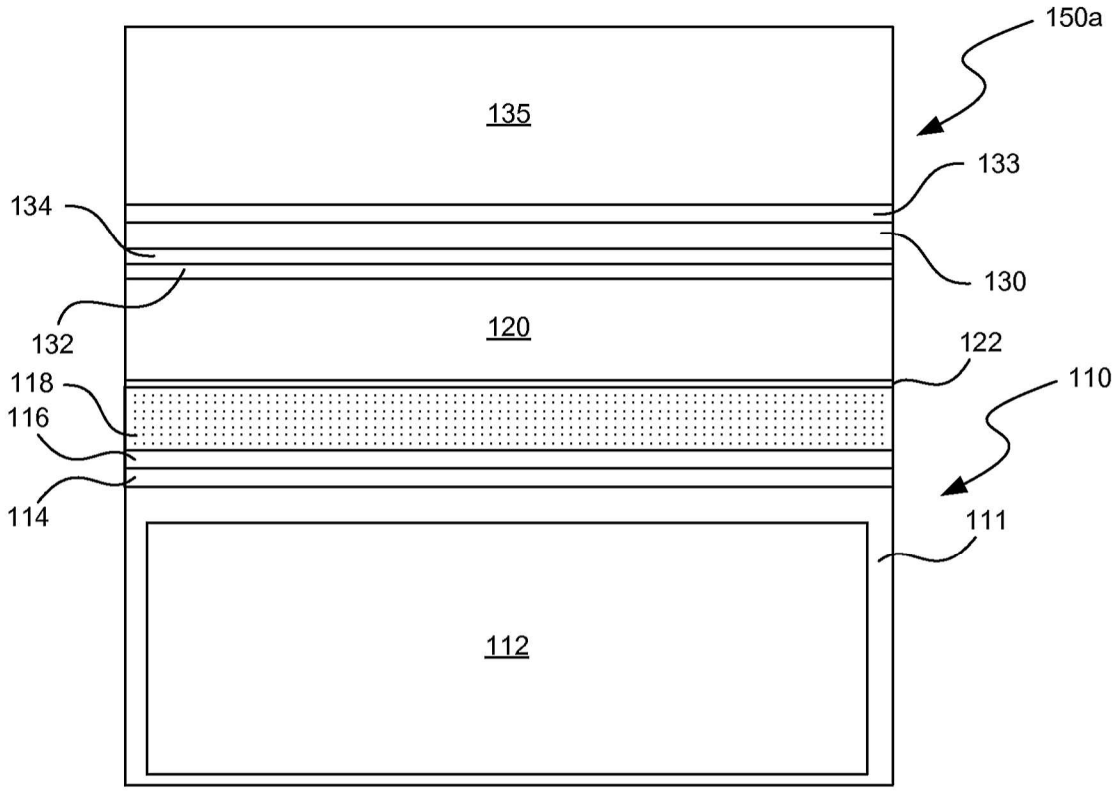

150a
135
133
134
130
132
120
122
118
110
116
114
111
112

FIG. 7A

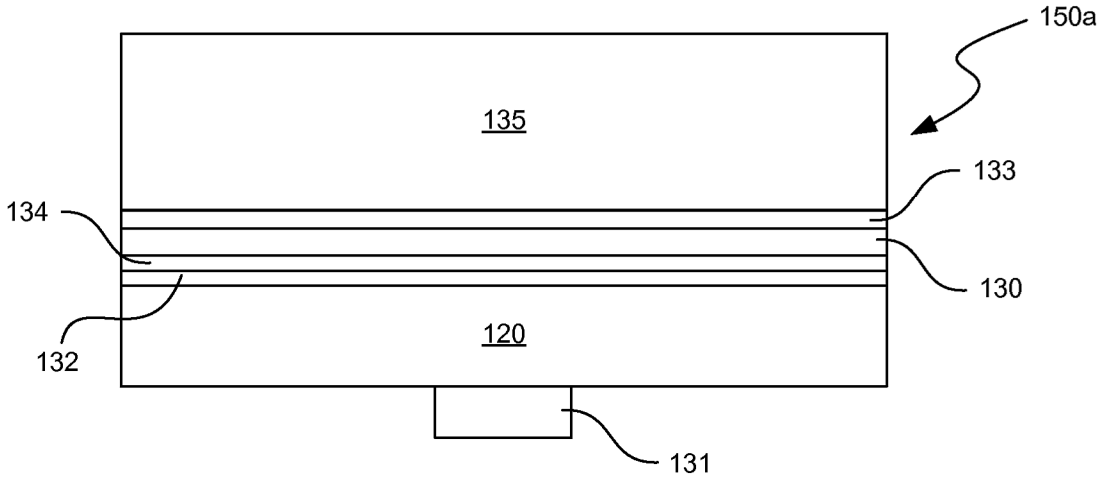

150a
135
133
134
130
120
132
131

FIG. 7B

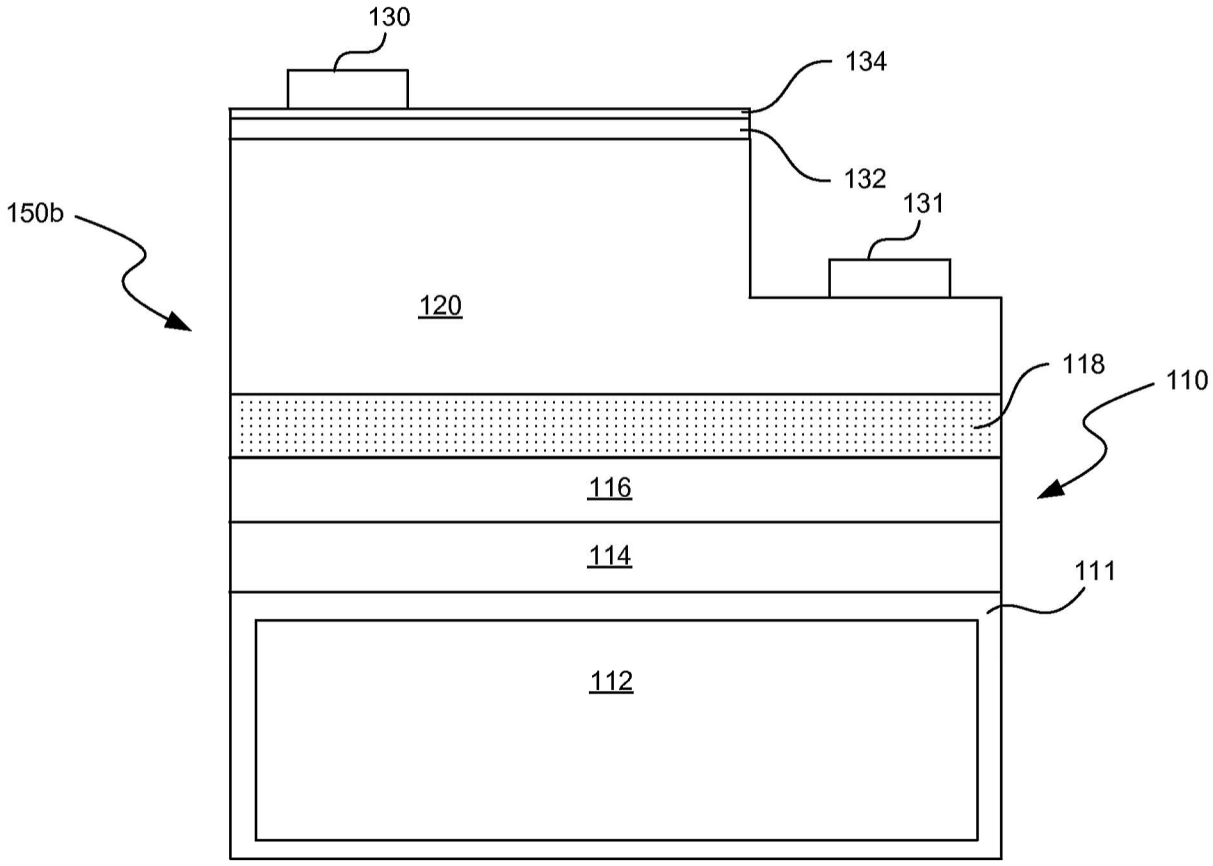


FIG. 8